DOCKET NO. SC13207TP

UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT

Dharesh Jawarani

GROUP ART UNIT: 2891

APPLN. NO.:

10/797,222

EXAMINER:

Victor V. Yevsikov

FILED:

MAR 3 0 2006

March 10, 2004

CONFIRMATION No.: 4099

TITLE:

METHOD OF INHIBITING METAL SILICIDE

ENCROACHMENT IN A TRANSISTOR

Certificate of Transmission under 37 C.F.R 1.8

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<u> 3.30.06</u>

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COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This paper is filed contemporaneous with the filing of the issue fee for this application. Entrance of the comments provided below regarding the statement of reasons for allowance provided by the Examiner is respectfully requested.

FEES

Applicants authorize the charging of Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any fees owed in connection with this application, or credit Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any refunds.

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REMARKS

In a communication mailed March 20, 2006, claims 1-28 were allowed. The Examiner provided a statement of reasons for allowance of the claims which Applicants believe is overly focused on one single claim recital. Applicants are submitting these comments in supplement of the reasons for allowance. The claim language which has been allowed recites novel features than the recited one of "implanting encroachment inhibiting ions into the transistor after selectively removing the unsilicided portions of the metal layer". For example, the prior art made of record does not teach the combination of annealing and material removal in combination with the use of inhibiting ions as recited in each of the independent claims. Further, Applicant submits that other unreferenced dependent claim features are also novel when combined with the whole of the claim limitations.

SEND CORRESPONDENCE TO:

Freescale Semiconductor, Inc.

Law Department

Customer Number: 23125

Respectfully submitted,

Robert L. King

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LAW DEPARTMENT FREESCALE SEMICONDUCTOR, INC.

DATE: March <u>30</u>, 2006

TO: MS: ISSUE FEE (703) 308-6789

(ADDRESSEE) (EXTENSION)

<u>USPTO</u> (571) 273-2885 (LOCATION) (FAX NUMBER)

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Docket No.: SC13207TP

Applicant: Dharesh Jawarani

Serial No.: 10/797,222

Art Unit:

2891

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March 10, 2004

Class: 438-592000

ALL ITEMS MARKED WITH AN "X" ARE INCLUDED;

L	1.		хl	1 page Facsimile Cover Sheet	
	2.		ΧĪ	1 page PTOL-85B Issue Fee Transmittal ((in duplicate)
3. X 2 page Comments on Statement of Reasons for Allowance			×Τ	ons for Allowance	
_	- :				

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If Applicant has overlooked any additional fees, or if any overpayment has been made, the Commissioner is hereby authorized to credit or debit Deposit Account 503079. Freescale Semiconductor, Inc.

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